

IN THE SPECIFICATION

Please replace the two paragraphs beginning at Page 3, line 14, and running through Page 4, line 8 in the originally filed specification with the following:

Specifically, in a plot 130 of plasma concentration versus surface locations as shown in Figure 1D, plasma sheaths edges are defined at points 133a and 133b along a plasma density profile 133. The plasma density profile 133 illustrates that the plasma concentration falls to about zero near the wafer surface 136 and at the top electrode surface 134. As such, the plasma concentration gradually increases from zero up to a constant concentration between points 133a and 133b. The electrode surface 134 and the wafer surface 136 will therefore ensure that the bulk of the plasma is contained between the plasma sheaths 131 and 132 as shown in Figure 1C.

As the demand to etch smaller and smaller integrated circuit device patterns continues to increase, more difficult high aspect ratio etching will be needed. As shown in Figure 1E, a cross sectional view 141 of a wafer substrate 106' is shown. The wafer substrate 106' has a dielectric layer 140 deposited thereon and a patterned photoresist layer 142. The photoresist layer 142 has a patterned window 144 defining a window down to the dielectric layer 140. As aspect ratios continue to increase (*i.e.*, deeper and narrower etching geometries), a process window that defines a set of controllable process parameters will also rapidly shrink. When the process window shrinks, adjustment of process parameters will no longer improve etch rates, etch selectivities, or etch profiles.

Please replace the Abstract of the Disclosure with the following:

Disclosed is a method for making an electrode for use in a system for processing a semiconductor wafer through plasma etching operations. The electrode has a center region, a first surface and a second surface, and is positioned within the system and over the semiconductor wafer. The second surface has a plurality of gas feed holes that are